

DN8899/SE/TE/S

Hall IC (Operating Temperature Range
 $T_{opr} = -40$ to $+100^{\circ}\text{C}$,
 Operating in Alternative Magnetic Field)

■ Overview

The DN8899/SE/TE/S is a combination of a Hall element, amplifier, Schmitt circuit, and stabilized power supply/temperature compensator integrated on an identical chip by using the IC technology. It amplifies Hall element output at the amplifier, converts into a digital signal through the Schmitt circuit, and drives the TTL or MOS IC directly.

■ Features

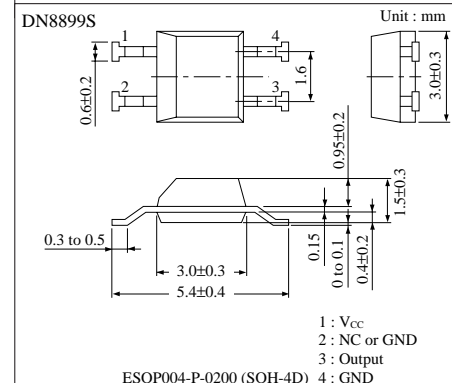
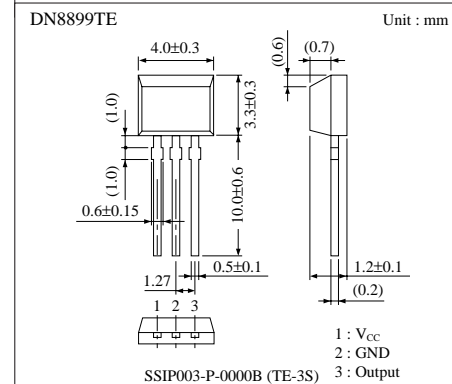
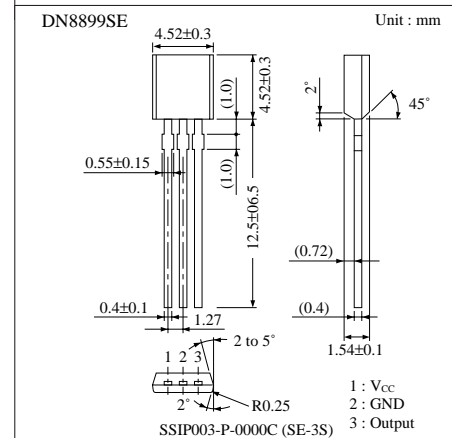
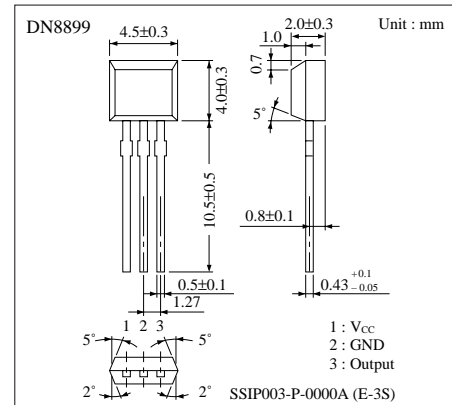
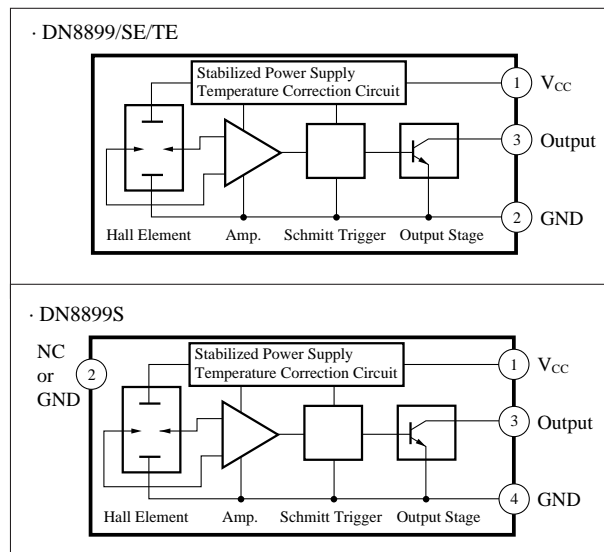
- High sensitivity and low drift
- Stable temperature characteristics due to the additional temperature compensator
- Wide operating supply voltage range ($V_{CC} = 4.5$ to 16V)
- Operating in alternative magnetic field
- TTL and MOS ICs directly drivable by output
- Semipermanent service life due to no contact parts
- Small change of the operating flux density against mechanical stress
- Output open collector
- "0" gauss point in the zero cross type hysteresis width

■ Applications

- Speed sensors
- Position sensors
- Rotation sensors
- Keyboard switches
- Microswitches

Note) This IC is not suitable for the car electric equipment.

■ Block Diagram



■ Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Rating	Unit
Supply voltage	V_{CC}	18	V
Supply current	I_{CC}	8	mA
Circuit current	I_O	20	mA
Power dissipation	P_D	150	mW
Operating ambient temperature	T_{opr}	-40 to +100	°C
Storage temperature	T_{stg}	-55 to +125	°C

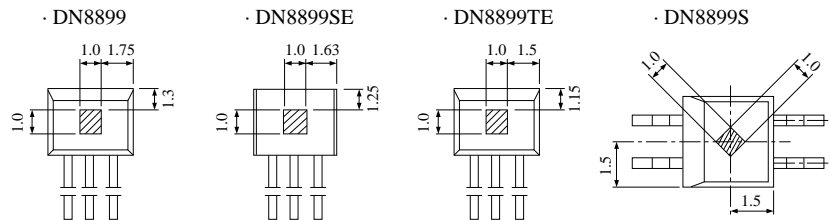
■ Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Condition	min	typ	max	Unit
Operating flux density	B_1 (L→H)	$V_{CC}=12V$	-12	-6	-0.1	mT
	B_2 (H→L)	$V_{CC}=12V$	0.1	6	12	mT
Hysteresis width	BW	$V_{CC}=12V$	7	10	—	mT
Low output voltage	V_{OL}	$V_{CC}=4.5$ to 16V, $I_O=12mA$, $B=12mT$	—	—	0.4	V
High output current	I_{OH}	$V_{CC}=4.5$ to 16V, $V_O=16V$, $B=-12mT$	—	—	10	μA
Supply current	I_{CC}	$V_{CC}=16V$	—	—	6	mA
		$V_{CC}=4.5V$	—	—	5.5	mA

■ Hall Element Position

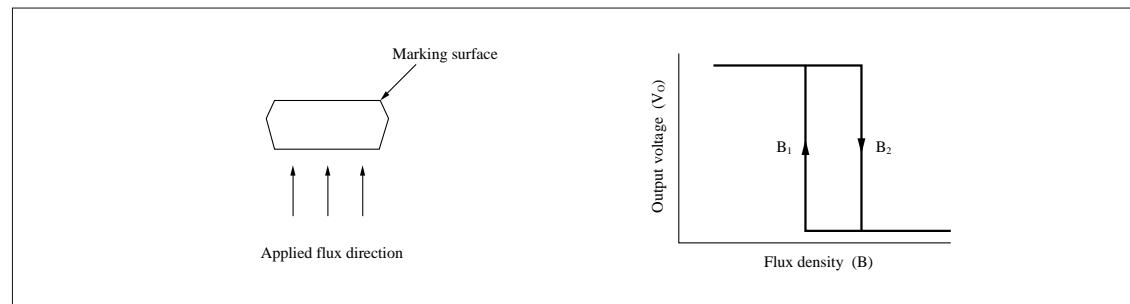
Unit : mm

The center of the Hall element is in the hatched area in the right figure.



Distance from package surface to sensor (mm)	DN8899	DN8899SE	DN8899TE	DN8899S
		0.7	0.42	0.4

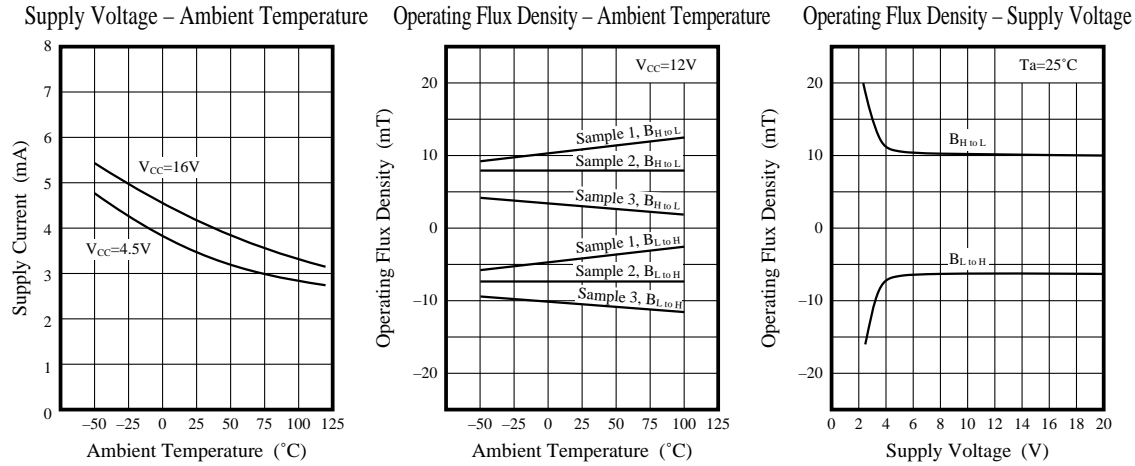
■ Flux-Voltage Conversion Characteristics



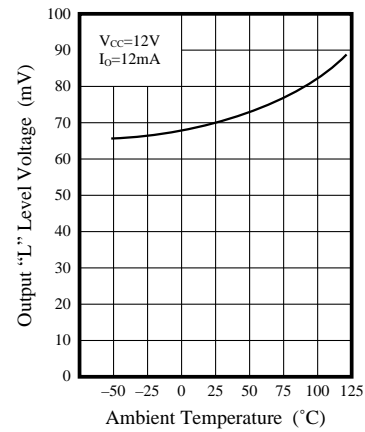
■ Supplementary Descriptions

1. Change of the operation magnetic flux density dose not depend on the supply voltage, because the stabilization power supply is built in. (only for the range ; $V_{CC}=4.5$ to $16V$)
2. Change from "H" to "L" level increases the supply current by approx. 1mA.

■ Characteristics Curve



Output Low Level Voltage – Ambient Temperature



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